

3.3 V/5 V ECL Differential Receiver/Driver with High Gain



ON Semiconductor®

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MC100EP16VA

Description

The EP16VA is a world-class differential receiver/driver. The device is functionally equivalent to the EP16 and LVEP16 devices but with high gain output. Q_{HG} and \overline{Q}_{HG} outputs have a DC gain several times larger than the DC gain of an EP16.

The V_{BB} pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to V_{BB} as a switching reference voltage. V_{BB} may also rebias AC coupled inputs. When used, decouple V_{BB} and V_{CC} via a 0.01 μ F capacitor and limit current sourcing or sinking to 0.5 mA. When not used, V_{BB} should be left open.

Under open input conditions (pulled to V_{EE}) internal input clamps will force the Q_{HG} output LOW.

Special considerations are required for differential inputs under No Signal conditions to prevent instability.

The 100 Series contains temperature compensation.

Features

- 270 ps Typical Propagation Delay
- Gain = > 20
- 20 mV Minimum Input Voltage Swing
- Maximum Frequency = > 3 GHz Typical
- PECL Mode Operating Range:
 $V_{CC} = 3.0$ V to 5.5 V with $V_{EE} = 0$ V
- NECL Mode Operating Range:
 $V_{CC} = 0$ V with $V_{EE} = -3.0$ V to -5.5 V
- Open Input Default State
- V_{BB} Output
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

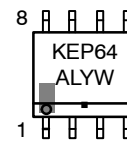


SOIC-8 NB
D SUFFIX
CASE 751-07

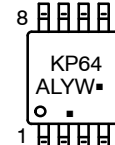


TSSOP-8
DT SUFFIX
CASE 948R-02

MARKING DIAGRAMS*



SOIC-8 NB



TSSOP-8

- K = MC100
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note [AND8002/D](#).

ORDERING INFORMATION

Device	Package	Shipping†
MC100EP16VADG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC100EP16VADTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100EP16VADTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

MC100EP16VA

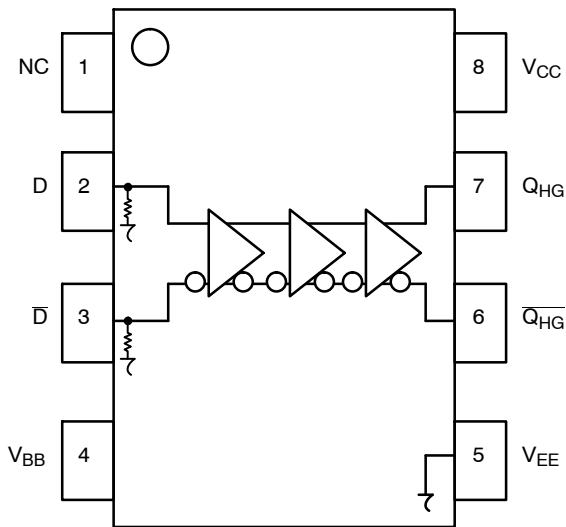


Table 1. PIN DESCRIPTION

PIN	FUNCTION
D*, \overline{D}^*	ECL Data Inputs
Q_{HG} , \overline{Q}_{HG}	ECL High Gain Data Outputs
V _{BB}	Reference Voltage Output
V _{CC}	Positive Supply
V _{EE}	Negative Supply
NC	No Connect

* Pins will default LOW when left open.

Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8	Level 1 Level 3
Flammability Rating Oxygen Index: 28 to 34	UL-94 V-0 @ 0.125 in
Transistor Count	167
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note [AND8003/D](#).

MC100EP16VA

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	PECL Mode Power Supply	$V_{EE} = 0\text{ V}$		6	V
V_{EE}	NECL Mode Power Supply	$V_{CC} = 0\text{ V}$		-6	V
V_I	PECL Mode Input Voltage NECL Mode Input Voltage	$V_{EE} = 0\text{ V}$ $V_{CC} = 0\text{ V}$	$V_I \leq V_{CC}$ $V_I \geq V_{EE}$	6 -6	V
I_{out}	Output Current	Continuous Surge		50 100	mA
I_{BB}	V_{BB} Sink/Source			± 0.5	mA
T_A	Operating Temperature Range			-40 to +85	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range			-65 to +150	$^{\circ}\text{C}$
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB SOIC-8 NB	190 130	$^{\circ}\text{C}/\text{W}$
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	$^{\circ}\text{C}/\text{W}$
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8 TSSOP-8	185 140	$^{\circ}\text{C}/\text{W}$
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	$^{\circ}\text{C}/\text{W}$
T_{sol}	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260 $^{\circ}\text{C}$		265	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

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Table 4. 100EP DC CHARACTERISTICS, PECL ($V_{CC} = 3.3\text{ V}$, $V_{EE} = 0\text{ V}$ (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V_{OL}	Output LOW Voltage (Note 2)	1305	1430	1555	1305	1430	1555	1305	1430	1555	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
V_{IL}	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
V_{BB}	Output Voltage Reference	1775	1875	1975	1775	1875	1975	1775	1875	1975	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		3.3	2.0		3.3	2.0		3.3	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.3 V to -2.2 V.
2. All loading with 50 Ω to $V_{CC} - 2.0\text{ V}$.
3. V_{IHCMR} min varies 1:1 with V_{EE} . V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 5. 100EP DC CHARACTERISTICS, PECL ($V_{CC} = 5.0\text{ V}$, $V_{EE} = 0\text{ V}$ (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	3855	3980	4105	3855	3980	4105	3855	3980	4105	mV
V_{OL}	Output LOW Voltage (Note 2)	3005	3180	3355	3005	3180	3355	3005	3180	3355	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	3775		4120	3775		4120	3775		4120	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3055		3375	3055		3375	3055		3375	mV
V_{BB}	Output Voltage Reference	3475	3575	3675	3475	3575	3675	3475	3575	3675	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		5.0	2.0		5.0	2.0		5.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +2.0 V to -0.5 V.
2. All loading with 50 Ω to $V_{CC} - 2.0\text{ V}$.
3. V_{IHCMR} min varies 1:1 with V_{EE} . V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

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Table 6. 100EP DC CHARACTERISTICS, NECL ($V_{CC} = 0\text{ V}$; $V_{EE} = -5.5\text{ V}$ to -3.0 V (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V_{OL}	Output LOW Voltage (Note 2)	-1995	-1870	-1745	-1995	-1870	-1745	-1995	-1870	-1745	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	-1225		-880	-1225		-880	-1225		-880	mV
V_{IL}	Input LOW Voltage (Single-Ended)	-1945		-1625	-1945		-1625	-1945		-1625	mV
V_{BB}	Output Voltage Reference	-1525	-1425	-1325	-1525	-1425	-1325	-1525	-1425	-1325	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	$V_{EE}+2.0$		0.0	$V_{EE}+2.0$		0.0	$V_{EE}+2.0$		0.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Input and output parameters vary 1:1 with V_{CC} .
2. All loading with $50\ \Omega$ to $V_{CC} - 2.0\text{ V}$.
3. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 7. AC CHARACTERISTICS ($V_{CC} = 0\text{ V}$; $V_{EE} = -3.0\text{ V}$ to -5.5 V or $V_{CC} = 3.0\text{ V}$ to 5.5 V ; $V_{EE} = 0\text{ V}$ (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{max}	Maximum Frequency (See Figure 2 $F_{max}/JITTER$)		> 3			> 3			> 3		GHz
t_{PLH} , t_{PHL}	Propagation Delay to Output Differential	200	260	320	220	270	340	250	320	390	ps
t_{SKEW}	Duty Cycle Skew (Note 2)		5.0	20		5.0	20		5.0	20	ps
t_{JITTER}	Cycle-to-Cycle Jitter (See Figure 2 $F_{max}/JITTER$)		0.2	< 1		0.2	< 1		0.2	< 1	ps
V_{PP}	Input Voltage Swing (Differential Configuration) (See Figure 3)	20	800	1200	20	800	1200	20	800	1200	mV
t_r , t_f	Output Rise/Fall Times Q, \bar{Q} (20% - 80%)	70	110	170	80	110	180	80	120	200	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Measured using a 750 mV source, 50% duty cycle clock source. All loading with $50\ \Omega$ to $V_{CC}-2.0\text{ V}$.
2. Skew is measured between outputs under identical transitions. Duty cycle skew is defined only for differential operation when the delays are measured from the cross point of the inputs to the cross point of the outputs.

MC100EP16VA

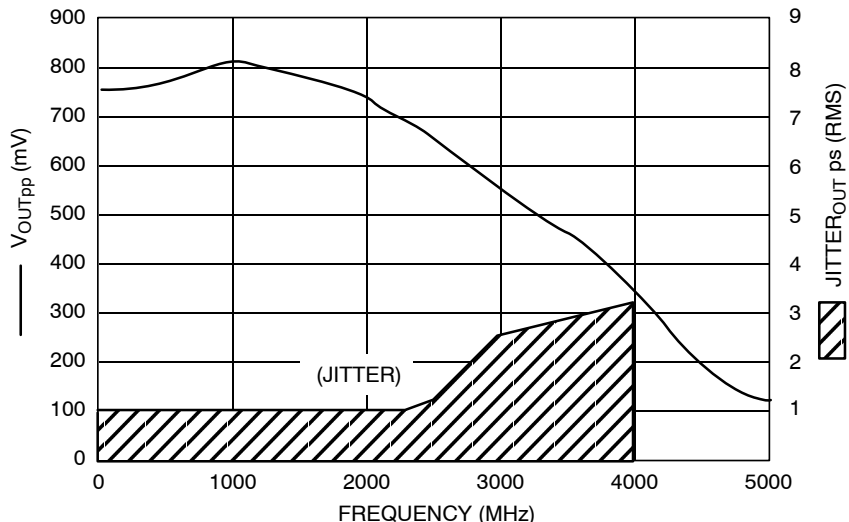


Figure 2. $F_{max}/Jitter$

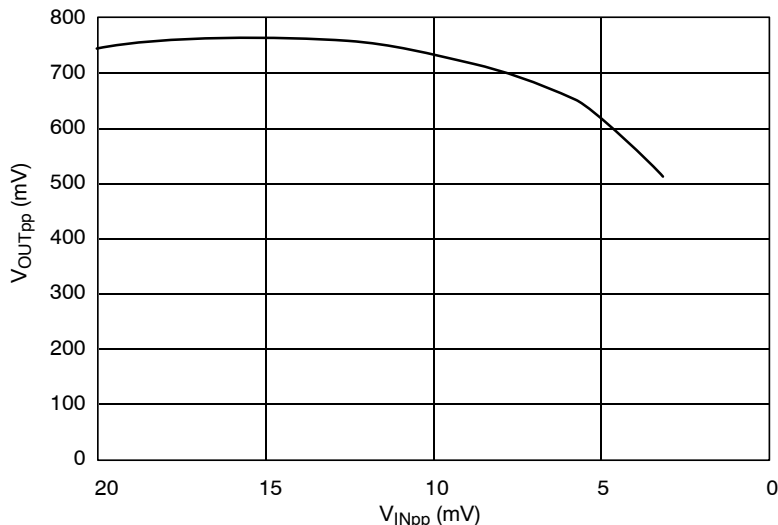


Figure 3. Gain vs. Input Voltage (50 MHz)

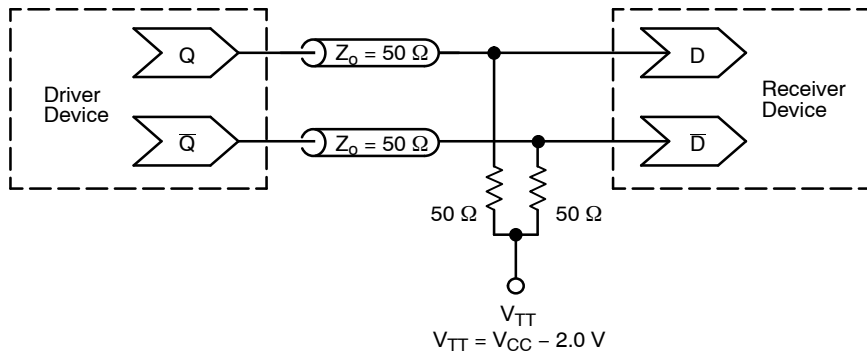


Figure 4. Typical Termination for Output Driver and Device Evaluation
(See Application Note [AND8020/D](#) – Termination of ECL Logic Devices)

Resource Reference of Application Notes

- AN1405/D** – ECL Clock Distribution Techniques
- AN1406/D** – Designing with PECL (ECL at +5.0 V)
- AN1503/D** – ECLinPS™ I/O SPiCE Modeling Kit
- AN1504/D** – Metastability and the ECLinPS Family
- AN1568/D** – Interfacing Between LVDS and ECL
- AN1672/D** – The ECL Translator Guide
- AND8001/D** – Odd Number Counters Design
- AND8002/D** – Marking and Date Codes
- AND8020/D** – Termination of ECL Logic Devices
- AND8066/D** – Interfacing with ECLinPS
- AND8090/D** – AC Characteristics of ECL Devices

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011

- | | | | |
|---|--|--|--|
| <p>STYLE 1:
 PIN 1. EMITTER
 2. COLLECTOR
 3. COLLECTOR
 4. EMITTER
 5. EMITTER
 6. BASE
 7. BASE
 8. EMITTER</p> | <p>STYLE 2:
 PIN 1. COLLECTOR, DIE, #1
 2. COLLECTOR, #1
 3. COLLECTOR, #2
 4. COLLECTOR, #2
 5. BASE, #2
 6. EMITTER, #2
 7. BASE, #1
 8. EMITTER, #1</p> | <p>STYLE 3:
 PIN 1. DRAIN, DIE #1
 2. DRAIN, #1
 3. DRAIN, #2
 4. DRAIN, #2
 5. GATE, #2
 6. SOURCE, #2
 7. GATE, #1
 8. SOURCE, #1</p> | <p>STYLE 4:
 PIN 1. ANODE
 2. ANODE
 3. ANODE
 4. ANODE
 5. ANODE
 6. ANODE
 7. ANODE
 8. COMMON CATHODE</p> |
| <p>STYLE 5:
 PIN 1. DRAIN
 2. DRAIN
 3. DRAIN
 4. DRAIN
 5. GATE
 6. GATE
 7. SOURCE
 8. SOURCE</p> | <p>STYLE 6:
 PIN 1. SOURCE
 2. DRAIN
 3. DRAIN
 4. SOURCE
 5. SOURCE
 6. GATE
 7. GATE
 8. SOURCE</p> | <p>STYLE 7:
 PIN 1. INPUT
 2. EXTERNAL BYPASS
 3. THIRD STAGE SOURCE
 4. GROUND
 5. DRAIN
 6. GATE 3
 7. SECOND STAGE Vd
 8. FIRST STAGE Vd</p> | <p>STYLE 8:
 PIN 1. COLLECTOR, DIE #1
 2. BASE, #1
 3. BASE, #2
 4. COLLECTOR, #2
 5. COLLECTOR, #2
 6. EMITTER, #2
 7. EMITTER, #1
 8. COLLECTOR, #1</p> |
| <p>STYLE 9:
 PIN 1. EMITTER, COMMON
 2. COLLECTOR, DIE #1
 3. COLLECTOR, DIE #2
 4. EMITTER, COMMON
 5. EMITTER, COMMON
 6. BASE, DIE #2
 7. BASE, DIE #1
 8. EMITTER, COMMON</p> | <p>STYLE 10:
 PIN 1. GROUND
 2. BIAS 1
 3. OUTPUT
 4. GROUND
 5. GROUND
 6. BIAS 2
 7. INPUT
 8. GROUND</p> | <p>STYLE 11:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. DRAIN 2
 7. DRAIN 1
 8. DRAIN 1</p> | <p>STYLE 12:
 PIN 1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 13:
 PIN 1. N.C.
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> | <p>STYLE 14:
 PIN 1. N-SOURCE
 2. N-GATE
 3. P-SOURCE
 4. P-GATE
 5. P-DRAIN
 6. P-DRAIN
 7. N-DRAIN
 8. N-DRAIN</p> | <p>STYLE 15:
 PIN 1. ANODE 1
 2. ANODE 1
 3. ANODE 1
 4. ANODE 1
 5. CATHODE, COMMON
 6. CATHODE, COMMON
 7. CATHODE, COMMON
 8. CATHODE, COMMON</p> | <p>STYLE 16:
 PIN 1. EMITTER, DIE #1
 2. BASE, DIE #1
 3. EMITTER, DIE #2
 4. BASE, DIE #2
 5. COLLECTOR, DIE #2
 6. COLLECTOR, DIE #2
 7. COLLECTOR, DIE #1
 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17:
 PIN 1. VCC
 2. V2OUT
 3. V1OUT
 4. TXE
 5. RXE
 6. VEE
 7. GND
 8. ACC</p> | <p>STYLE 18:
 PIN 1. ANODE
 2. ANODE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. CATHODE
 8. CATHODE</p> | <p>STYLE 19:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. MIRROR 2
 7. DRAIN 1
 8. MIRROR 1</p> | <p>STYLE 20:
 PIN 1. SOURCE (N)
 2. GATE (N)
 3. SOURCE (P)
 4. GATE (P)
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 21:
 PIN 1. CATHODE 1
 2. CATHODE 2
 3. CATHODE 3
 4. CATHODE 4
 5. CATHODE 5
 6. COMMON ANODE
 7. COMMON ANODE
 8. CATHODE 6</p> | <p>STYLE 22:
 PIN 1. I/O LINE 1
 2. COMMON CATHODE/VCC
 3. COMMON CATHODE/VCC
 4. I/O LINE 3
 5. COMMON ANODE/GND
 6. I/O LINE 4
 7. I/O LINE 5
 8. COMMON ANODE/GND</p> | <p>STYLE 23:
 PIN 1. LINE 1 IN
 2. COMMON ANODE/GND
 3. COMMON ANODE/GND
 4. LINE 2 IN
 5. LINE 2 OUT
 6. COMMON ANODE/GND
 7. COMMON ANODE/GND
 8. LINE 1 OUT</p> | <p>STYLE 24:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR/ANODE
 4. COLLECTOR/ANODE
 5. CATHODE
 6. CATHODE
 7. COLLECTOR/ANODE
 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25:
 PIN 1. VIN
 2. N/C
 3. REXT
 4. GND
 5. IOUT
 6. IOUT
 7. IOUT
 8. IOUT</p> | <p>STYLE 26:
 PIN 1. GND
 2. dv/dt
 3. ENABLE
 4. ILIMIT
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. VCC</p> | <p>STYLE 27:
 PIN 1. ILIMIT
 2. OVLO
 3. UVLO
 4. INPUT+
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. DRAIN</p> | <p>STYLE 28:
 PIN 1. SW_TO_GND
 2. DASIC_OFF
 3. DASIC_SW_DET
 4. GND
 5. V_MON
 6. VBULK
 7. VBULK
 8. VIN</p> |
| <p>STYLE 29:
 PIN 1. BASE, DIE #1
 2. EMITTER, #1
 3. BASE, #2
 4. EMITTER, #2
 5. COLLECTOR, #2
 6. COLLECTOR, #2
 7. COLLECTOR, #1
 8. COLLECTOR, #1</p> | <p>STYLE 30:
 PIN 1. DRAIN 1
 2. DRAIN 1
 3. GATE 2
 4. SOURCE 2
 5. SOURCE 1/DRAIN 2
 6. SOURCE 1/DRAIN 2
 7. SOURCE 1/DRAIN 2
 8. GATE 1</p> | | |

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 2:1

TSSOP 8 CASE 948R-02 ISSUE A

DATE 04/07/2000



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0°	6°	0°	6°

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